

DESCRIPTION

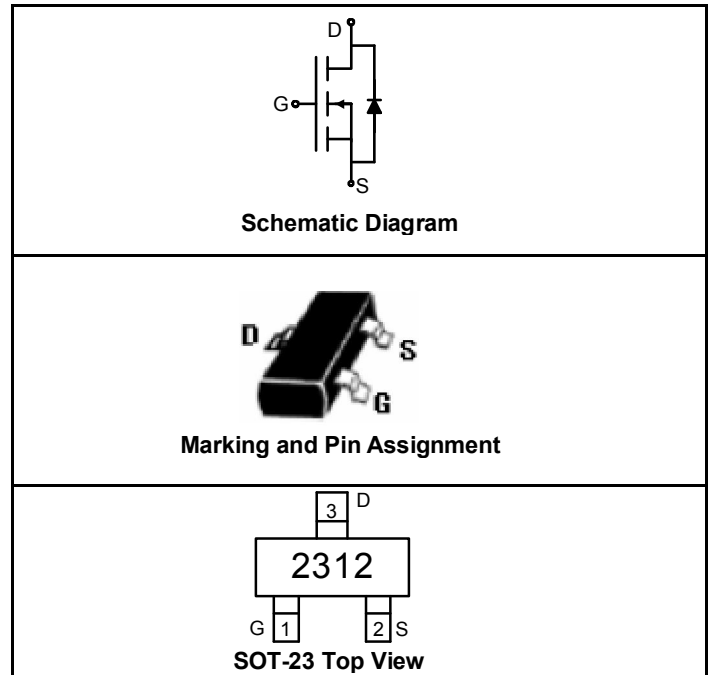
The SSF2312 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

GENERAL FEATURES

- $V_{DS} = 20V, I_D = 4.5A$
 $R_{DS(ON)} < 40m\Omega @ V_{GS}=2.5V$
 $R_{DS(ON)} < 33m\Omega @ V_{GS}=4.5V$
- High Power and current handling capability
- Lead free product
- Surface Mount Package

APPLICATIONS

- Battery protection
- Load switch
- Power management



PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape Width	Quantity
2312	SSF2312	SOT-23	Ø180mm	8 mm	3000 units

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	4.5	A
	I_{DM}	13.5	A
Maximum Power Dissipation	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	$^\circ C/W$
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ELECTRICAL CHARACTERISTICS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTICS (Note 3)						



SSF2312

20V N-Channel MOSFET

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.65	1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=2.5V, I_D=4.5A$		33	40	m Ω
		$V_{GS}=4.5V, I_D=5A$		27	33	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=5A$		10		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=8V, V_{GS}=0V,$ $F=1.0MHz$		500		PF
Output Capacitance	C_{oss}			300		PF
Reverse Transfer Capacitance	C_{rss}			140		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$		20	40	nS
Turn-on Rise Time	t_r			18	40	nS
Turn-Off Delay Time	$t_{d(off)}$			60	108	nS
Turn-Off Fall Time	t_f			28	56	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=5A, V_{GS}=4.5V$		10	15	nC
Gate-Source Charge	Q_{gs}			2.3		nC
Gate-Drain Charge	Q_{gd}			2.9		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=1A$			1.2	V
Diode Forward Current (Note 2)	I_S				1	A

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

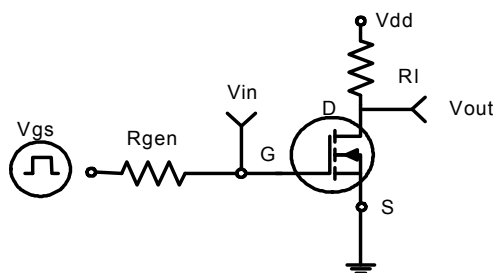


Figure 1: Switching Test Circuit

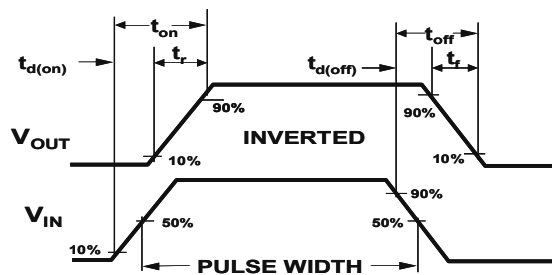


Figure 2: Switching Waveforms

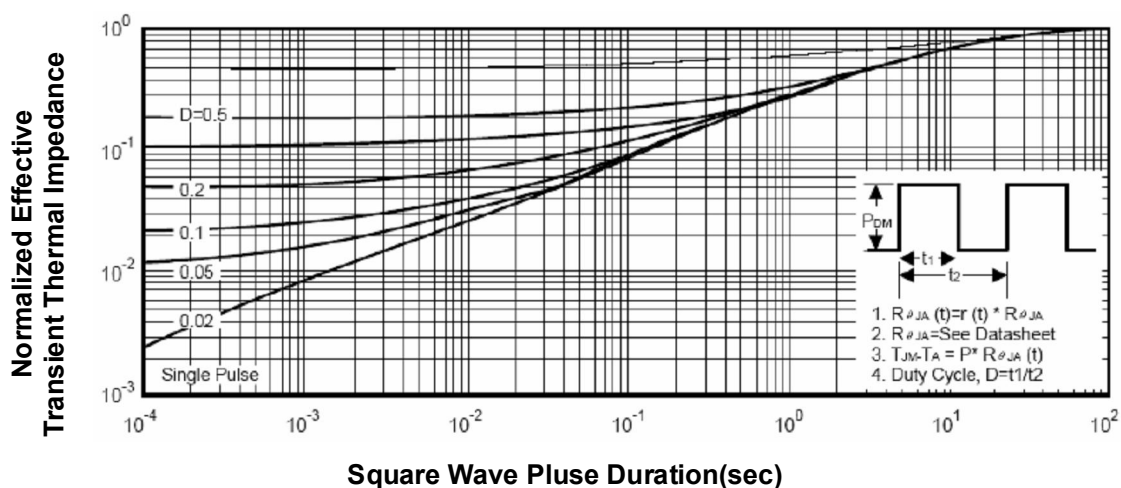
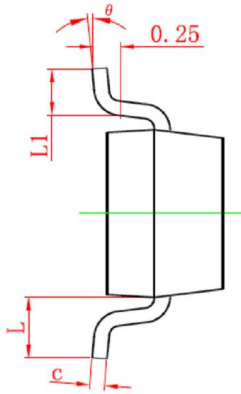
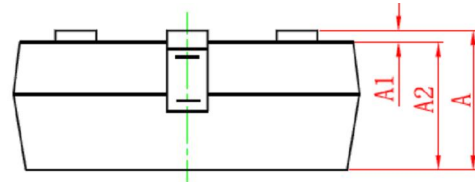
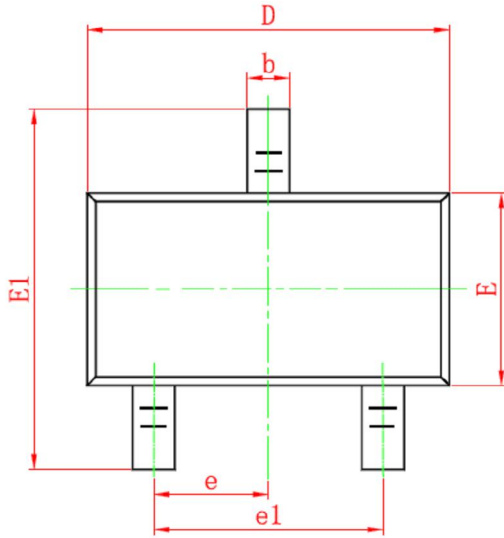


Figure 3: Normalized Maximum Transient Thermal Impedance

SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT: mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

NOTES

- All dimensions are in millimeters.
- Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
- Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- Dimension L is measured in gauge plane.
- Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.